







INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 990342A	Serial No. Not Yet Assigned
	Applicant(s): SHIMOYAMA, et al.	
	Filing Date: September 2, 2003	Group Art Unit: 2828 (expected)

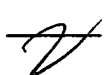
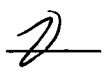

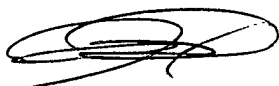
U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
	AA	5,003,549	Mitsui et al.	3/1991	372	46
	AB	5,465,266	Bour et al.	11/1995		
	AC	4,622,673	Tsang	11/1986	372	45

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Document No.	Date	Country	Translation (Yes or No)
 AD EP 0 867 949	9/30/98	European	
 AE EP 0 469 301	6/29/90	European	
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OTHER DOCUMENTS

	AG	LIN J-F ET AL: "High temperature and low threshold current operation of strained AlGaInP/Ga _{0.4} In _{0.6} P multiple quantum well laser diodes emitting at 676 nm" vol. 30, no. 6, pages 494-495, March 1994.
	AH	Patent Abstracts of Japan; vol. 017, no. 065 (E-1317); February 9, 1993 & JP 04 269886 A (Toshiba Corp.), 9/25/92).
	AI	Patent Abstracts of Japan; vol. 1997, no. 11, November 28, 1997 & JP 09 199791 A (NNEC Corp), July 31, 1997
Examiner 	Date Considered	4/5/04